

IMiD 2018

August 28 - 31, 2018 / BEXCO, Busan, Korea

Session Title: 15. Si Transistors I
Date: Aug. 29 (Wed.), 2018
Time: 10:50~12:10
Room: G (Room 314~315)
Session Chairs: Prof. Naoto Matsuo (Univ. of Hyogo, Japan)
Prof. Yong-Hoon Kim (Sungkyunkwan Univ., Korea)

[G15-1] 10:50~11:15

[Invited] Poly-Si TFT Technology from Viewpoints of Low-Temperature Crystallization and High-Performance Device

Naoto Matsuo (Univ. of Hyogo, Japan)

[G15-2] 11:15~11:40

[Invited] Low Temperature Growth of Group-IV Semiconductors on Insulator for Advanced Flexible Electronics

Taizoh Sadoh, Masanobu Miyao (Kyushu Univ., Japan), and Isao Tsunoda (Kumamoto College, Japan)

[G15-3] 11:40~11:55

[Oral] Effective Laser Crystallization of PECVD Si Films without De-Hydrogenation

Takashi Noguchi, Yuya Ishiki, Tatsuya Okada (Univ. of the Ryukyus, Japan), Taro Morimura, Atsushi Ota, and Yasushi Nishikata (ULVAC, Japan)

[G15-4] 11:55~12:10

[Oral] Crystallization of Si Film on PC (Poly-Carbonate) for Low-Cost LTPS TFT Formed below 200°C

Yuya Ishiki, Futa Gakiya, Tatsuya Okada, Takashi Noguchi (Univ. of the Ryukyus, Japan), and Naoya Kawamoto (Yamaguchi Univ., Japan)